

Hollow Dielectric for Image Sensor

ABSTRACT OF THE DISCLOSURE

A plurality of apertures is formed in at least one first insulating layer disposed over a sensor formed in a semiconductor substrate. A second insulating layer is disposed over the at least one first insulating layer and the plurality of apertures in the at least one first insulating layer. The apertures form hollow regions in the at least one first insulating layer over the sensor, allowing more light or energy to pass through the at least one first insulating layer to the sensor, and increasing the sensitivity of the sensor.

(FIG. 2)